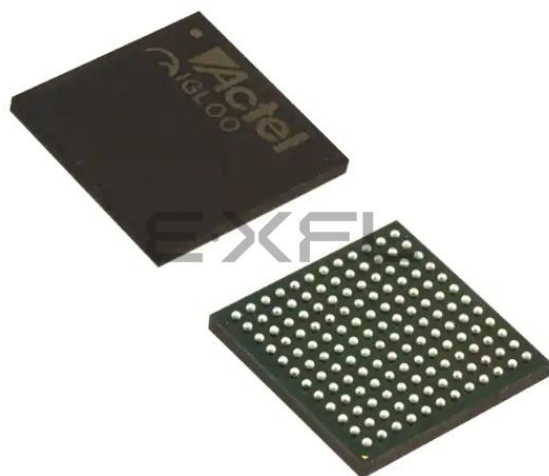




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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	24576
Total RAM Bits	147456
Number of I/O	97
Number of Gates	1000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1agl1000v2-fgg144i

Table 2-17 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings¹
Applicable to Standard Plus I/O Banks

	C _{LOAD} (pF)	V _{CCI} (V)	Static Power PDC7 (mW) ²	Dynamic Power PAC10 (μW/MHz) ³
Single-Ended				
3.3 V LVTTTL / 3.3 V LVCMOS	5	3.3	–	122.16
3.3 V LVCMOS Wide Range ⁴	5	3.3	–	122.16
2.5 V LVCMOS	5	2.5	–	68.37
1.8 V LVCMOS	5	1.8	–	34.53
1.5 V LVCMOS (JESD8-11)	5	1.5	–	23.66
1.2 V LVCMOS ⁵	5	1.2	–	14.90
1.2 V LVCMOS Wide Range ⁵	5	1.2	–	14.90
3.3 V PCI	10	3.3	–	181.06
3.3 V PCI-X	10	3.3	–	181.06

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. P_{DC7} is the static power (where applicable) measured on V_{CCI}.
3. P_{AC10} is the total dynamic power measured on V_{CCI}.
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
5. Applicable for IGLOO V2 devices only.

Table 2-18 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings¹
Applicable to Standard I/O Banks

	C _{LOAD} (pF)	V _{CCI} (V)	Static Power PDC7 (mW) ²	Dynamic Power PAC10 (μW/MHz) ³
Single-Ended				
3.3 V LVTTTL / 3.3 V LVCMOS	5	3.3	–	104.38
3.3 V LVCMOS Wide Range ⁴	5	3.3	–	104.38
2.5 V LVCMOS	5	2.5	–	59.86
1.8 V LVCMOS	5	1.8	–	31.26
1.5 V LVCMOS (JESD8-11)	5	1.5	–	21.96
1.2 V LVCMOS ⁵	5	1.2	–	13.49
1.2 V LVCMOS Wide Range ⁵	5	1.2	–	13.49

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. PDC7 is the static power (where applicable) measured on V_{CCI}.
3. PAC10 is the total dynamic power measured on V_{CCI}.
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
5. Applicable for IGLOO V2 devices only.

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-29 • Summary of AC Measuring Points

Standard	Measuring Trip Point (Vtrip)
3.3 V LVTTTL / 3.3 V LVCMOS	1.4 V
3.3 V VCMOS Wide Range	1.4 V
2.5 V LVCMOS	1.2 V
1.8 V LVCMOS	0.90 V
1.5 V LVCMOS	0.75 V
1.2 V LVCMOS	0.60 V
1.2 V LVCMOS Wide Range	0.60 V
3.3 V PCI	0.285 * VCCI (RR)
	0.615 * VCCI (FF)
3.3 V PCI-X	0.285 * VCCI (RR)
	0.615 * VCCI (FF)

Table 2-30 • I/O AC Parameter Definitions

Parameter	Parameter Definition
t_{DP}	Data to Pad delay through the Output Buffer
t_{PY}	Pad to Data delay through the Input Buffer
t_{DOUT}	Data to Output Buffer delay through the I/O interface
t_{EOUT}	Enable to Output Buffer Tristate Control delay through the I/O interface
t_{DIN}	Input Buffer to Data delay through the I/O interface
t_{HZ}	Enable to Pad delay through the Output Buffer—High to Z
t_{ZH}	Enable to Pad delay through the Output Buffer—Z to High
t_{LZ}	Enable to Pad delay through the Output Buffer—Low to Z
t_{ZL}	Enable to Pad delay through the Output Buffer—Z to Low
t_{ZHS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to High
t_{ZLS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to Low

Table 2-35 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case V_{CCI} (per standard)
Applicable to Standard Plus I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ¹ (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{BOUT} (ns)	t_{BP} (ns)	t_{BIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12	High	5	–	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns
3.3 V LVCMOS Wide Range ²	100 μA	12	High	5	–	1.55	3.20	0.26	1.32	1.10	3.20	2.52	4.01	4.97	8.99	8.31	ns
2.5 V LVCMOS	12 mA	12	High	5	–	1.55	2.29	0.26	1.19	1.10	2.32	1.94	2.94	3.52	8.10	7.73	ns
1.8 V LVCMOS	8 mA	8	High	5	–	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns
1.5 V LVCMOS	4 mA	4	High	5	–	1.55	2.68	0.26	1.27	1.10	2.72	2.39	3.07	3.37	8.50	8.18	ns
1.2 V LVCMOS	2 mA	2	High	5	–	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns
1.2 V LVCMOS Wide Range ³	100 μA	2	High	5	–	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns
3.3 V PCI	Per PCI spec	–	High	10	25^2	1.55	2.53	0.26	0.84	1.10	2.57	1.98	2.93	3.64	8.35	7.76	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25^2	1.55	2.53	0.25	0.85	1.10	2.57	1.98	2.93	3.64	8.35	7.76	ns

Notes:

1. The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification
4. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.
5. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Single-Ended I/O Characteristics

3.3 V LVTTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTTL input buffer and push-pull output buffer. Furthermore, all LVCMOS 3.3 V software macros comply with LVCMOS 3.3 V wide range as specified in the JESD8a specification.

Table 2-47 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	132	127	10	10
24 mA	−0.3	0.8	2	3.6	0.4	2.4	24	24	268	181	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-48 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	103	109	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

Table 2-79 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.7	1.7	2.7	0.7	1.7	2	2	16	18	10	10
4 mA	−0.3	0.7	1.7	2.7	0.7	1.7	4	4	16	18	10	10
6 mA	−0.3	0.7	1.7	2.7	0.7	1.7	6	6	32	37	10	10
8 mA	−0.3	0.7	1.7	2.7	0.7	1.7	8	8	32	37	10	10
12 mA	−0.3	0.7	1.7	2.7	0.7	1.7	12	12	65	74	10	10
16 mA	−0.3	0.7	1.7	2.7	0.7	1.7	16	16	83	87	10	10
24 mA	−0.3	0.7	1.7	2.7	0.7	1.7	24	24	169	124	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-80 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.7	1.7	2.7	0.7	1.7	2	2	16	18	10	10
4 mA	−0.3	0.7	1.7	2.7	0.7	1.7	4	4	16	18	10	10
6 mA	−0.3	0.7	1.7	2.7	0.7	1.7	6	6	32	37	10	10
8 mA	−0.3	0.7	1.7	2.7	0.7	1.7	8	8	32	37	10	10
12 mA	−0.3	0.7	1.7	2.7	0.7	1.7	12	12	65	74	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Applies to 1.2 V Core Voltage**Table 2-89 • 2.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
4 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
6 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
8 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
12 mA	Std.	1.55	4.17	0.26	1.20	1.10	4.23	3.99	3.30	3.67	10.02	9.77	ns
16 mA	Std.	1.55	3.98	0.26	1.20	1.10	4.04	3.88	3.34	3.76	9.83	9.66	ns
24 mA	Std.	1.55	3.90	0.26	1.20	1.10	3.96	3.90	3.40	4.09	9.75	9.68	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-90 • 2.5 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
4 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
6 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
8 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
12 mA	Std.	1.55	2.64	0.26	1.20	1.10	2.67	2.29	3.30	3.79	8.46	8.08	ns
16 mA	Std.	1.55	2.59	0.26	1.20	1.10	2.63	2.24	3.34	3.88	8.41	8.03	ns
24 mA	Std.	1.55	2.60	0.26	1.20	1.10	2.64	2.18	3.40	4.22	8.42	7.97	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-91 • 2.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
 Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
4 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
6 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
8 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
12 mA	Std.	1.55	3.66	0.26	1.19	1.10	3.71	3.55	2.94	3.41	9.50	9.34	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-92 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	2.91	0.26	1.19	1.10	2.95	2.66	2.50	2.72	8.74	8.45	ns
4 mA	Std.	1.55	2.91	0.26	1.19	1.10	2.95	2.66	2.50	2.72	8.74	8.45	ns
6 mA	Std.	1.55	2.51	0.26	1.19	1.10	2.54	2.18	2.75	3.21	8.33	7.97	ns
8 mA	Std.	1.55	2.51	0.26	1.19	1.10	2.54	2.18	2.75	3.21	8.33	7.97	ns
12 mA	Std.	1.55	2.29	0.26	1.19	1.10	2.32	1.94	2.94	3.52	8.10	7.73	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-93 • 2.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	4.85	0.26	1.15	1.10	4.93	4.55	2.13	2.24	ns
4 mA	Std.	1.55	4.85	0.26	1.15	1.10	4.93	4.55	2.13	2.24	ns
6 mA	Std.	1.55	4.09	0.26	1.15	1.10	4.16	3.95	2.38	2.71	ns
8 mA	Std.	1.55	4.09	0.26	1.15	1.10	4.16	3.95	2.38	2.71	ns

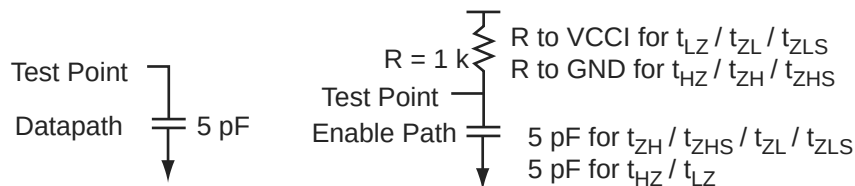
Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-94 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	2.76	0.26	1.15	1.10	2.80	2.52	2.13	2.32	ns
4 mA	Std.	1.55	2.76	0.26	1.15	1.10	2.80	2.52	2.13	2.32	ns
6 mA	Std.	1.55	2.39	0.26	1.15	1.10	2.42	2.05	2.38	2.80	ns
8 mA	Std.	1.55	2.39	0.26	1.15	1.10	2.42	2.05	2.38	2.80	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

**Figure 2-11 • AC Loading****Table 2-130 • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.2	0.6	5

Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.

Timing Characteristics

1.2 V DC Core Voltage

Table 2-131 • 1.2 V LVCMOS Low Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	8.37	0.26	1.60	1.10	8.04	7.17	3.94	3.52	13.82	12.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-132 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-133 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	7.59	0.26	1.59	1.10	7.29	6.54	3.30	3.35	13.08	12.33	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-134 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

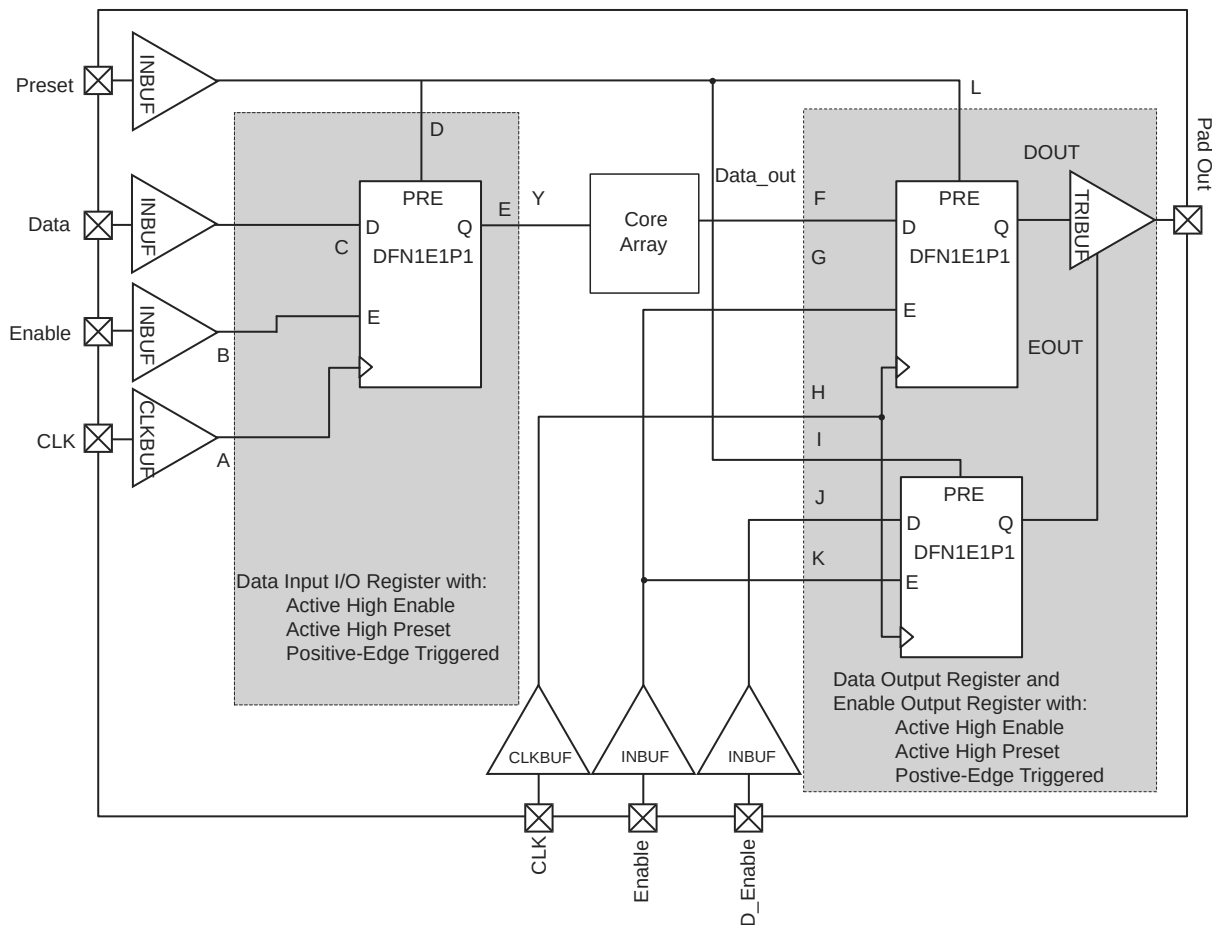


Figure 2-16 • Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The IGLOO library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide*.

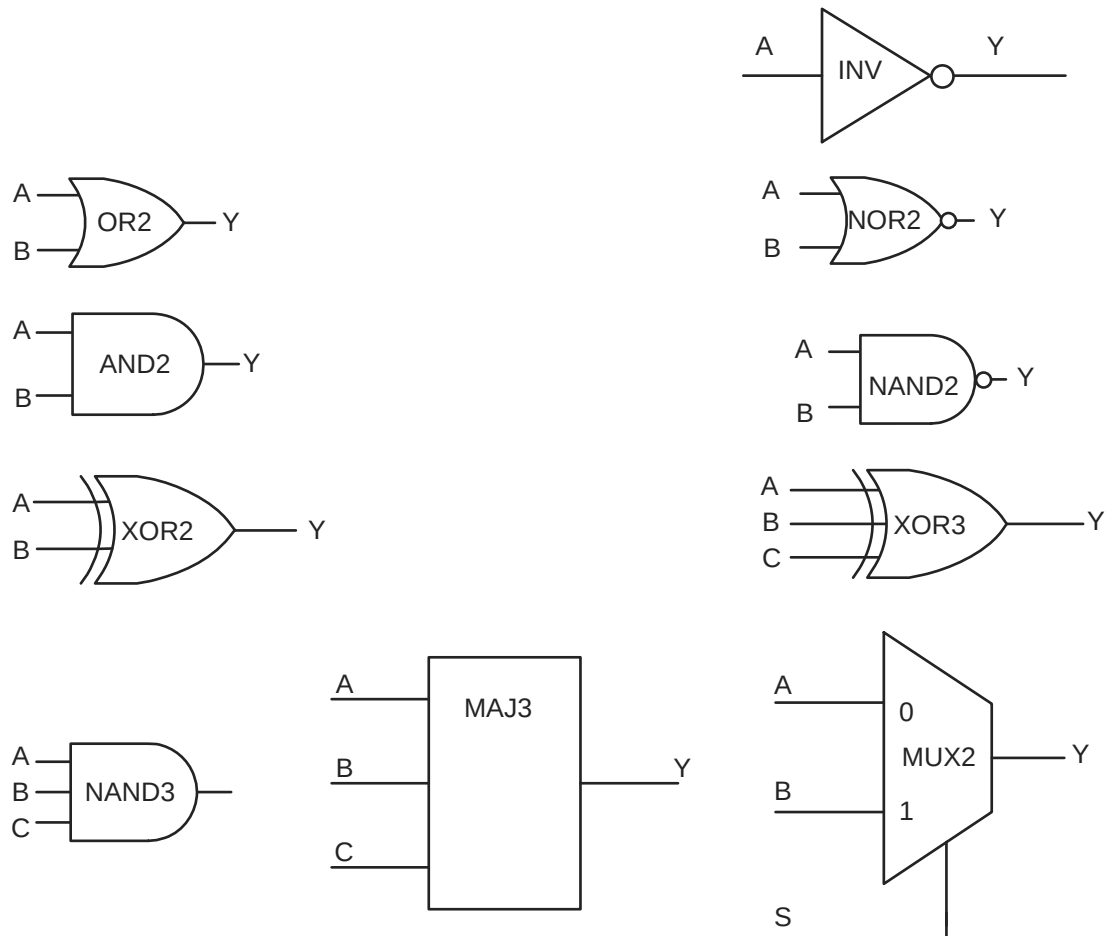


Figure 2-25 • Sample of Combinatorial Cells

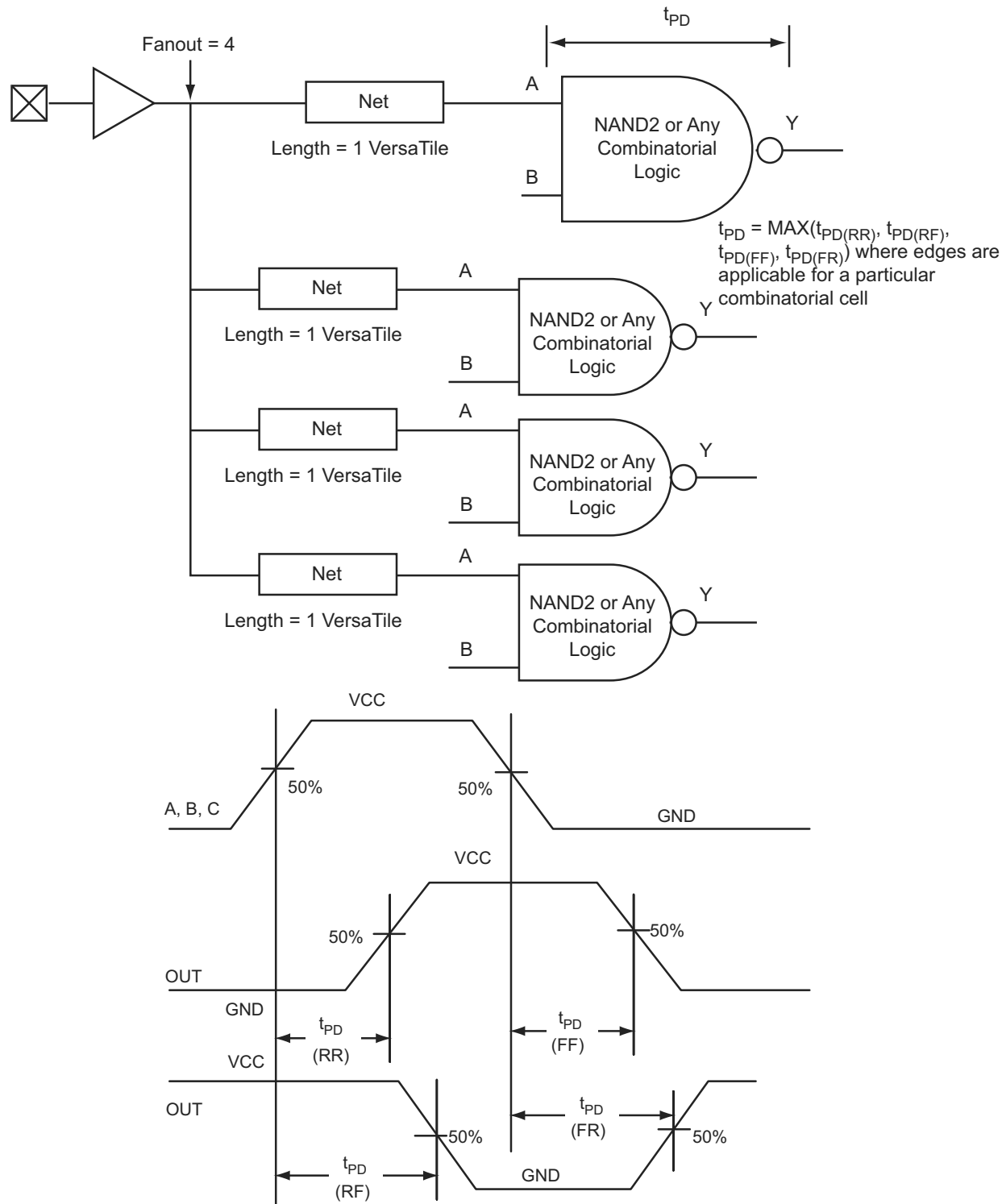


Figure 2-26 • Timing Model and Waveforms

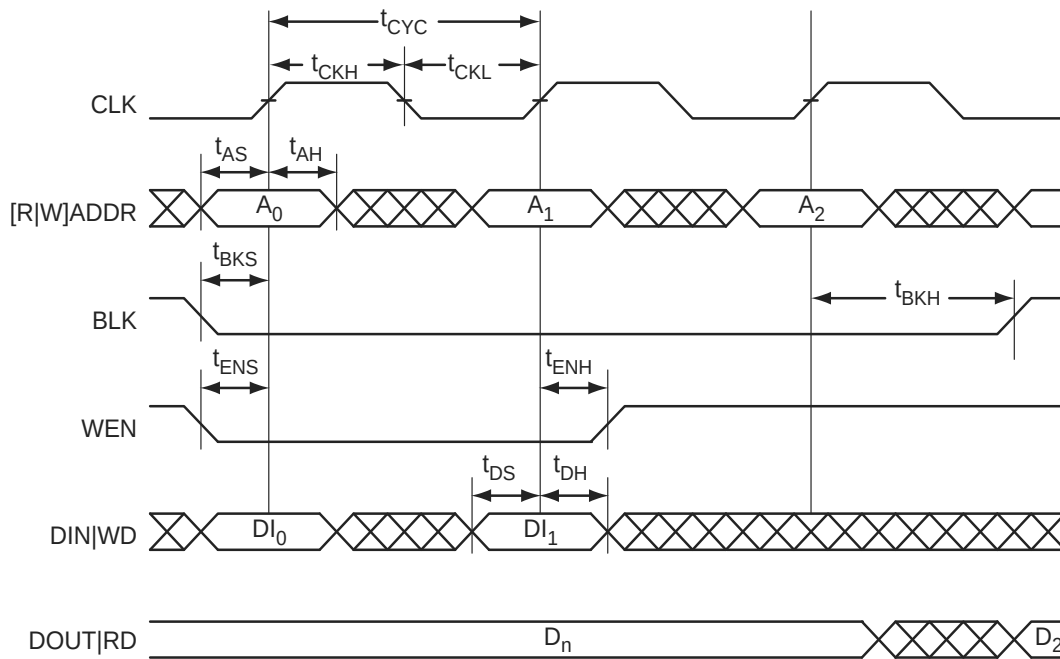


Figure 2-34 • RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.

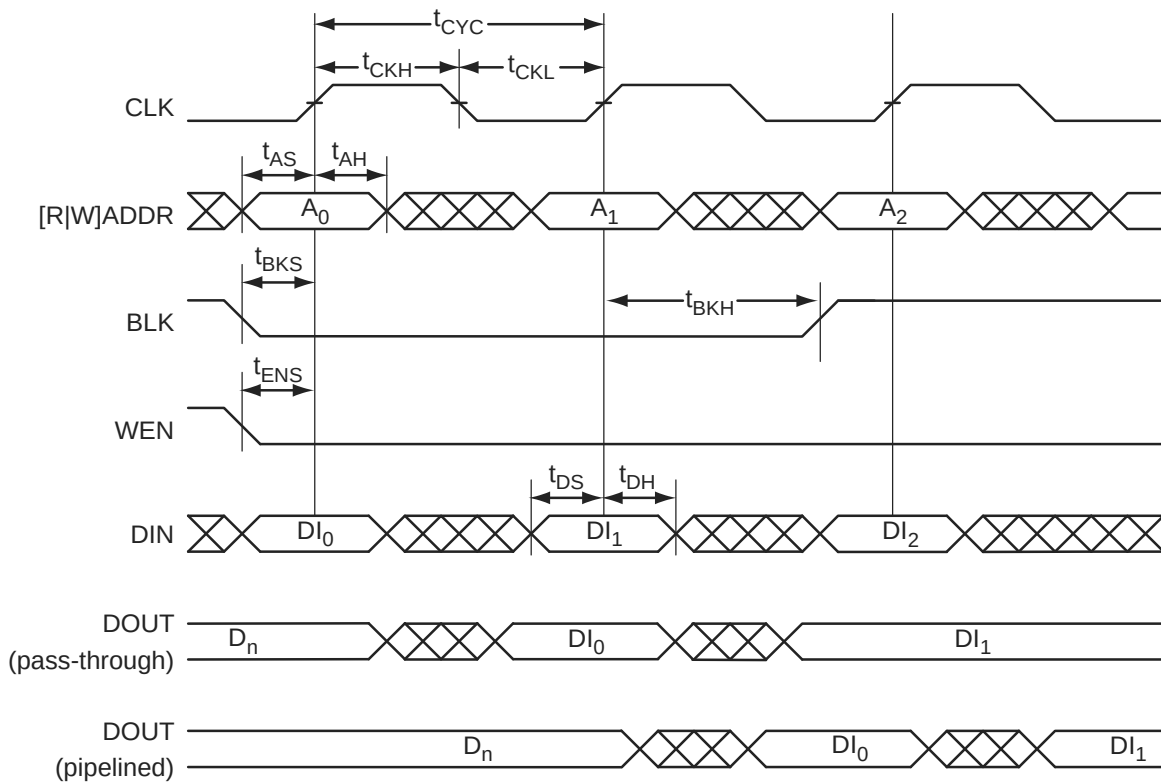


Figure 2-35 • RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 only.

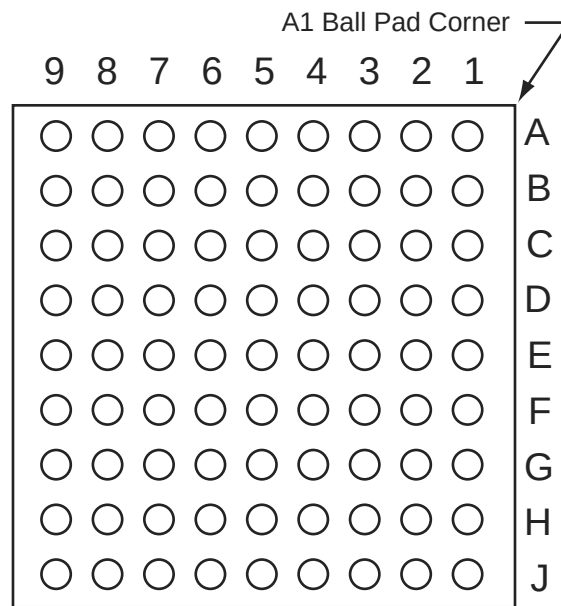
Table 2-192 • RAM512X18**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.83	ns
t_{AH}	Address hold time	0.16	ns
t_{ENS}	REN, WEN setup time	0.73	ns
t_{ENH}	REN, WEN hold time	0.08	ns
t_{DS}	Input data (WD) setup time	0.71	ns
t_{DH}	Input data (WD) hold time	0.36	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	4.21	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	1.71	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address - Applicable to Opening Edge	0.35	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address - Applicable to Opening Edge	0.42	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	2.06	ns
	RESET Low to data out Low on RD (pipelined)	2.06	ns
$t_{REMRSTB}$	RESET removal	0.61	ns
$t_{RECRSTB}$	RESET recovery	3.21	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

CS81



Note: This is the bottom view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

CS81	
Pin Number	AGL030 Function
A1	IO00RSB0
A2	IO02RSB0
A3	IO06RSB0
A4	IO11RSB0
A5	IO16RSB0
A6	IO19RSB0
A7	IO22RSB0
A8	IO24RSB0
A9	IO26RSB0
B1	IO81RSB1
B2	IO04RSB0
B3	IO10RSB0
B4	IO13RSB0
B5	IO15RSB0
B6	IO20RSB0
B7	IO21RSB0
B8	IO28RSB0
B9	IO25RSB0
C1	IO79RSB1
C2	IO80RSB1
C3	IO08RSB0
C4	IO12RSB0
C5	IO17RSB0
C6	IO14RSB0
C7	IO18RSB0
C8	IO29RSB0
C9	IO27RSB0
D1	IO74RSB1
D2	IO76RSB1
D3	IO77RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	IO23RSB0
D8	IO31RSB0
D9	IO30RSB0

CS81	
Pin Number	AGL030 Function
E1	GEB0/IO71RSB1
E2	GEA0/IO72RSB1
E3	GEC0/IO73RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GDC0/IO32RSB0
E8	GDA0/IO33RSB0
E9	GDB0/IO34RSB0
F1	IO68RSB1
F2	IO67RSB1
F3	IO64RSB1
F4	GND
F5	VCCIB1
F6	IO47RSB1
F7	IO36RSB0
F8	IO38RSB0
F9	IO40RSB0
G1	IO65RSB1
G2	IO66RSB1
G3	IO57RSB1
G4	IO53RSB1
G5	IO49RSB1
G6	IO44RSB1
G7	IO46RSB1
G8	VJTAG
G9	TRST
H1	IO62RSB1
H2	FF/IO60RSB1
H3	IO58RSB1
H4	IO54RSB1
H5	IO48RSB1
H6	IO43RSB1
H7	IO42RSB1
H8	TDI
H9	TDO

CS81	
Pin Number	AGL030 Function
J1	IO63RSB1
J2	IO61RSB1
J3	IO59RSB1
J4	IO56RSB1
J5	IO52RSB1
J6	IO45RSB1
J7	TCK
J8	TMS
J9	VPUMP

QN68	
Pin Number	AGL030 Function
1	IO82RSB1
2	IO80RSB1
3	IO78RSB1
4	IO76RSB1
5	GEC0/IO73RSB1
6	GEA0/IO72RSB1
7	GEB0/IO71RSB1
8	VCC
9	GND
10	VCCIB1
11	IO68RSB1
12	IO67RSB1
13	IO66RSB1
14	IO65RSB1
15	IO64RSB1
16	IO63RSB1
17	IO62RSB1
18	FF/IO60RSB1
19	IO58RSB1
20	IO56RSB1
21	IO54RSB1
22	IO52RSB1
23	IO51RSB1
24	VCC
25	GND
26	VCCIB1
27	IO50RSB1
28	IO48RSB1
29	IO46RSB1
30	IO44RSB1
31	IO42RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP
36	TDO

QN68	
Pin Number	AGL030 Function
37	TRST
38	VJTAG
39	IO40RSB0
40	IO37RSB0
41	GDB0/IO34RSB0
42	GDA0/IO33RSB0
43	GDC0/IO32RSB0
44	VCCIB0
45	GND
46	VCC
47	IO31RSB0
48	IO29RSB0
49	IO28RSB0
50	IO27RSB0
51	IO25RSB0
52	IO24RSB0
53	IO22RSB0
54	IO21RSB0
55	IO19RSB0
56	IO17RSB0
57	IO15RSB0
58	IO14RSB0
59	VCCIB0
60	GND
61	VCC
62	IO12RSB0
63	IO10RSB0
64	IO08RSB0
65	IO06RSB0
66	IO04RSB0
67	IO02RSB0
68	IO00RSB0

FG484	
Pin Number	AGL400 Function
B7	NC
B8	NC
B9	NC
B10	NC
B11	NC
B12	NC
B13	NC
B14	NC
B15	NC
B16	NC
B17	NC
B18	NC
B19	NC
B20	NC
B21	VCCIB1
B22	GND
C1	VCCIB3
C2	NC
C3	NC
C4	NC
C5	GND
C6	NC
C7	NC
C8	VCC
C9	VCC
C10	NC
C11	NC
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG484	
Pin Number	AGL1000 Function
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO91PPB1
K17	IO90NPB1
K18	IO88PDB1
K19	IO88NDB1
K20	IO94NPB1
K21	IO98NDB1
K22	IO98PDB1
L1	NC
L2	IO200PDB3
L3	IO210NPB3
L4	GFB0/IO208NPB3
L5	GFA0/IO207NDB3
L6	GFB1/IO208PPB3
L7	VCOMPLF
L8	GFC0/IO209NPB3
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO91NPB1
L16	GCB1/IO92PPB1
L17	GCA0/IO93NPB1
L18	IO96NPB1
L19	GCB0/IO92NPB1
L20	IO97PDB1
L21	IO97NDB1
L22	IO99NPB1
M1	NC
M2	IO200NDB3

5 – Datasheet Information

List of Changes

The following tables list critical changes that were made in each revision of the IGLOO datasheet.

Revision	Changes	Page
Revision 27 (May 2016)	Added the deleted package FG144 from AGL125 device in "IGLOO Devices" (SAR 79355).	1-I
Revision 26 (March 2016)	Updated "IGLOO Ordering Information" and "Temperature Grade Offerings" notes by: - Replacing Commercial (0°C to +70°C Ambient Temperature) with Commercial (0°C to +85°C Junction Temperature) (SAR 48352). - Replacing Industrial (-40°C to +85°C Ambient Temperature) with Industrial (-40°C to +100°C Junction Temperature) (SAR 48352).	1-III and 1-IV
	Ambient temperature row removed in Table 2-2 (SAR 48352).	2-2
	Updated Table 2-2 note 2 from "To ensure targeted reliability standards are met across ambient and junction operating temperatures, Microsemi recommends that the user follow best design practices using Microsemi's timing and power simulation tools." to "Software Default Junction Temperature Range in the Libero SoC software is set to 0°C to +70°C for commercial, and -40°C to +85°C for industrial. To ensure targeted reliability standards are met across the full range of junction temperatures, Microsemi recommends using custom settings for temperature range before running timing and power analysis tools. For more information on custom settings, refer to the New Project Dialog Box in the Libero SoC Online Help." (SAR 77087).	2-2
	Updated Table 2-2 note 9 from "VMV pins must be connected to the corresponding VCCI pins. See the "Pin Descriptions" chapter of the IGLOO FPGA Fabric User Guide for further information." to "VMV and VCCI must be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" on page 3-1 for further information." (SAR 77087)	2-2
	Added 2 mA drive strengths in tables same as 4 mA (SAR 57179).	NA
	Added reference of Package Mechanical Drawings document in all package pin assignment notes (76777).	NA
Revision 25 (June 2015)	Removed package FG144 from AGL060 device in the following tables: "IGLOO Devices", "I/Os Per Package1" and "Temperature Grade Offerings" (SAR 68517)	I, II, and IV
	Removed Package Pin Assignment table of AGL060 device from FG144.(SAR 68517)	-
Revision 24 (March 2014)	Note added for the discontinuance of QN132 package to the following tables: "IGLOO Devices", "I/Os Per Package1", "IGLOO FPGAs Package Sizes Dimensions", and "Temperature Grade Offerings" and "QN132" section (SAR 55117, PDN 1306).	I, II, IV, and 4-28
	Removed packages CS81 and QN132 from AGL250 device in the following tables: "IGLOO Devices", "I/Os Per Package1", and "Temperature Grade Offerings" (SAR 49472).	I, II, and IV

Revision / Version	Changes	Page
Revision 8 (cont'd)	Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings, Table 2-14 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings, Table 2-15 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings, and Table 2-16 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings ¹ were updated to change PDC2 to PDC6 and PDC3 to PDC7. The table notes were updated to reflect that power was measured on VCCI.	2-10 through 2-11
	In Table 2-19 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices, the description for PAC13 was changed from Static to Dynamic.	2-13
	Table 2-20 • Different Components Contributing to the Static Power Consumption in IGLOO Devices and Table 2-22 • Different Components Contributing to the Static Power Consumption in IGLOO Device were updated to add PDC6 and PDC7, and to change the definition for PDC5 to bank quiescent power. Subtitles were added to indicate type of devices and core supply voltage.	2-14, 2-16
	The "Total Static Power Consumption—PSTAT" section was updated to revise the calculation of P _{STAT} , including PDC6 and PDC7.	2-17
	Footnote † was updated to include information about PAC13. The PLL Contribution equation was changed from: $P_{PLL} = P_{AC13} + P_{AC14} * F_{CLKOUT}$ to $P_{PLL} = P_{DC4} + P_{AC13} * F_{CLKOUT}$.	2-18
Revision 7 (Jun 2008) Packaging v1.5	The "QN132" package diagram was updated to include D1 to D4. In addition, note 1 was changed from top view to bottom view, and note 2 is new.	4-28
Revision 6 (Jun 2008) Packaging v1.4	This document was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A
	Pin numbers were added to the "QN68" package diagram. Note 2 was added below the diagram.	4-25
Revision 5 (Mar 2008) Packaging v1.3	The "CS196" package and pin table was added for AGL250.	4-12
Revision 4 (Mar 2008) Product Brief v1.0	The "Low Power" section was updated to change "1.2 V and 1.5 V Core Voltage" to "1.2 V and 1.5 V Core and I/O Voltage." The text "(from 12 μW)" was removed from "Low Power Active FPGA Operation."	I
	1.2_V was added to the list of core and I/O voltages in the "Advanced I/O" and "I/Os with Advanced I/O Standards" section sections.	I, 1-7
	The "Embedded Memory" section was updated to remove the footnote reference from the section heading and place it instead after "4,608-Bit" and "True Dual-Port SRAM (except ×18)."	I